



(19) **United States**

(12) **Patent Application Publication**  
**Sasatani et al.**

(10) **Pub. No.: US 2004/0012332 A1**

(43) **Pub. Date: Jan. 22, 2004**

(54) **ELECTROLUMINESCENT DISPLAY DEVICE**

**Publication Classification**

(75) Inventors: **Toru Sasatani**, Motosu-gun (JP);  
**Tetsuji Omura**, Ogaki-shi (JP)

(51) **Int. Cl.<sup>7</sup> ..... H05B 33/00**

(52) **U.S. Cl. .... 313/506**

Correspondence Address:  
**MORRISON & FOERSTER LLP**  
**1650 TYSONS BOULEVARD**  
**SUITE 300**  
**MCLEAN, VA 22102 (US)**

(57) **ABSTRACT**

(73) Assignee: **Sanyo Electric Co., Ltd.**, Moriguchi-City (JP)

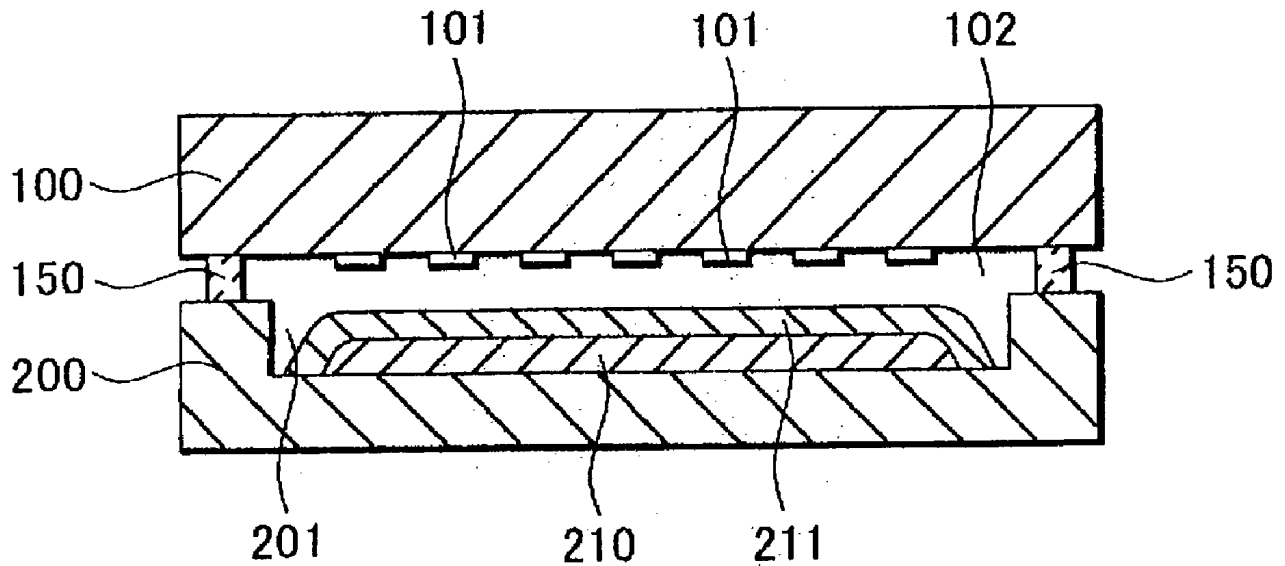
In a sealing structure of an electroluminescent display device, in which a first glass substrate formed with an EL element and a second glass substrate as a cap are attached to each other, breaking of the element device is prevented when external force is applied to the first glass substrate and the second glass substrate. The sealing structure has the first glass substrate provided with the EL element on a surface thereof, the second glass substrate attached to the first glass substrate with a sealing resin, a desiccant layer formed on a surface of the second glass substrate and a stress buffer layer covering a surface of the desiccant layer.

(21) Appl. No.: **10/419,982**

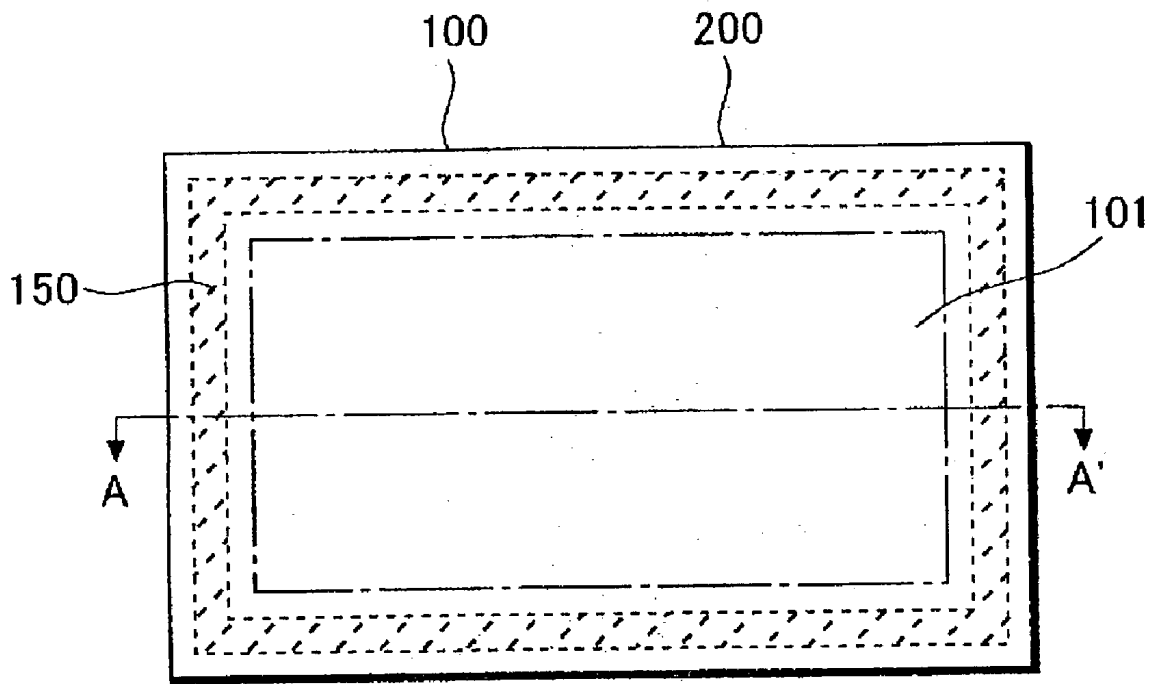
(22) Filed: **Apr. 22, 2003**

(30) **Foreign Application Priority Data**

Apr. 24, 2002 (JP) ..... 2002-122114



**FIG. 1**



**FIG. 2**

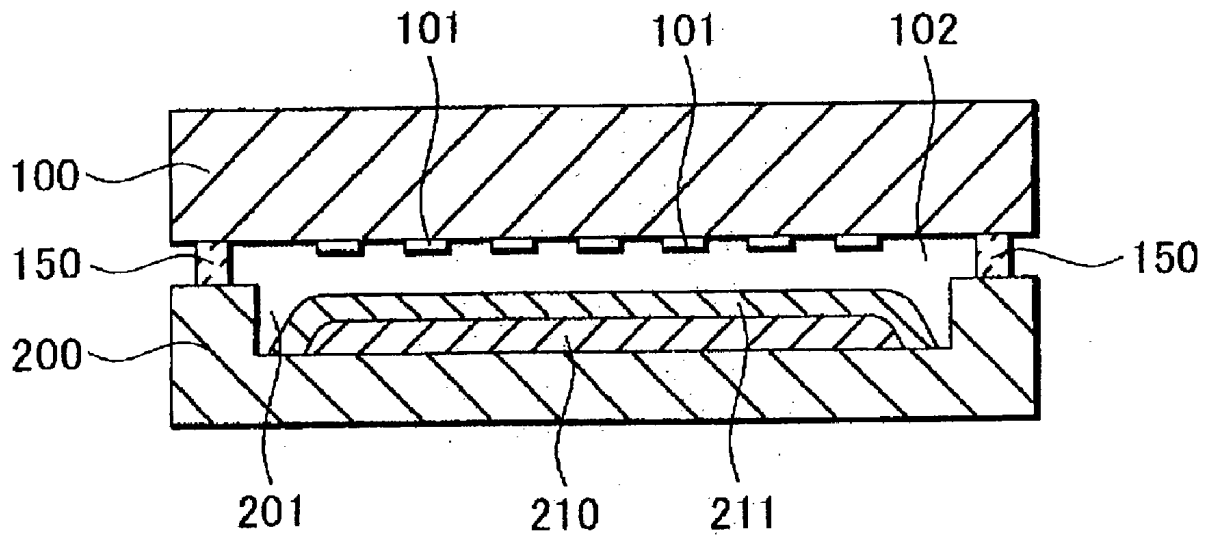


FIG. 3

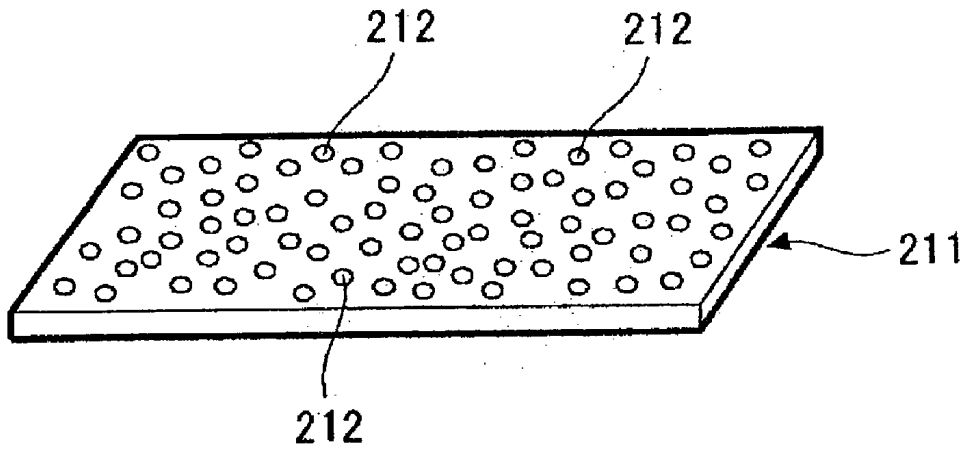
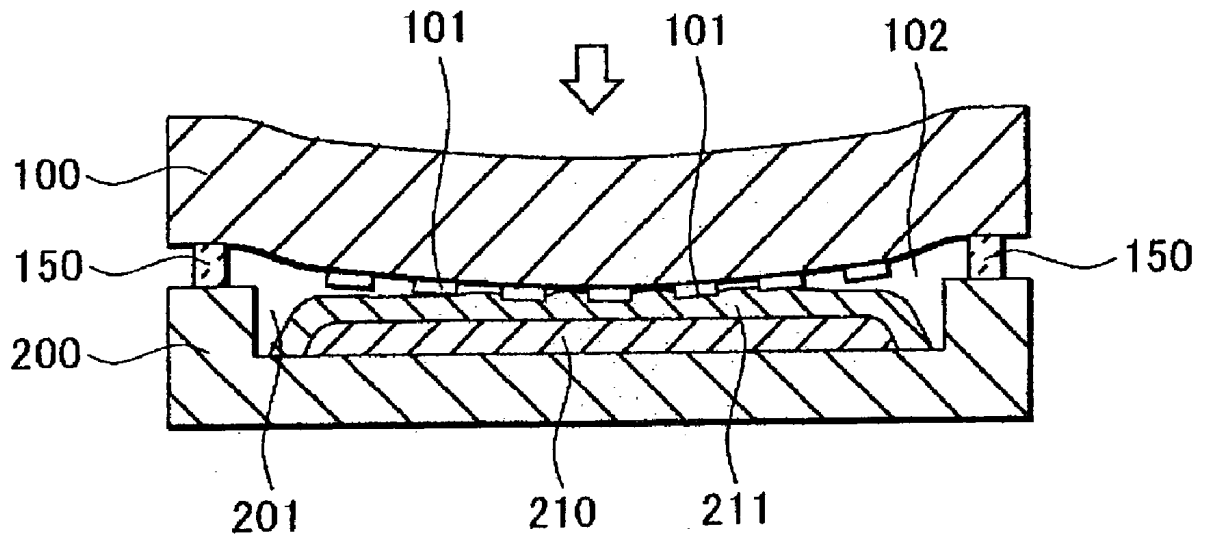
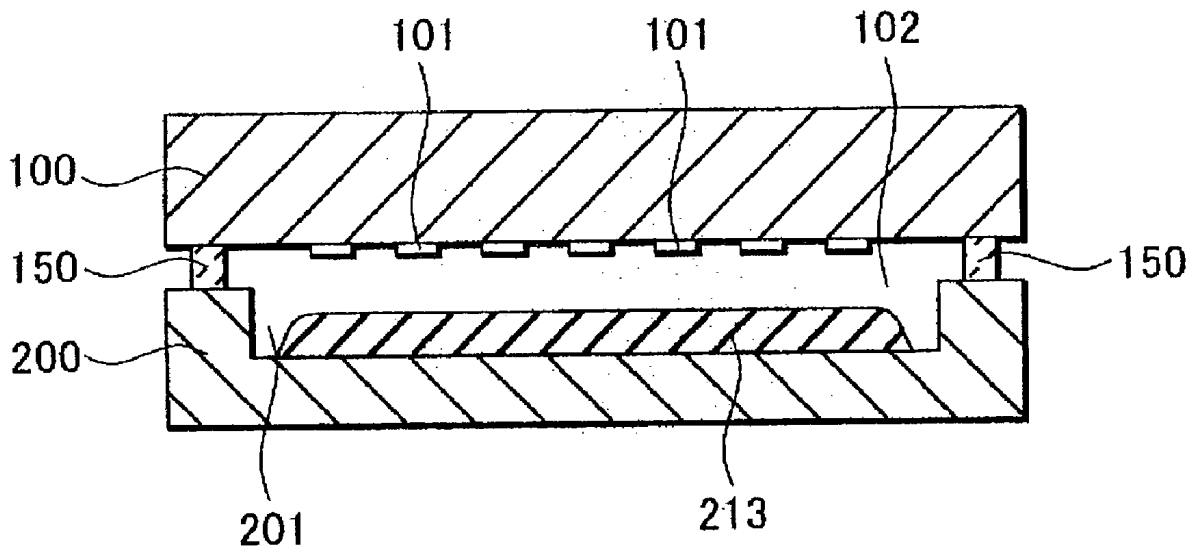


FIG. 4



**FIG. 5**



**FIG. 6**

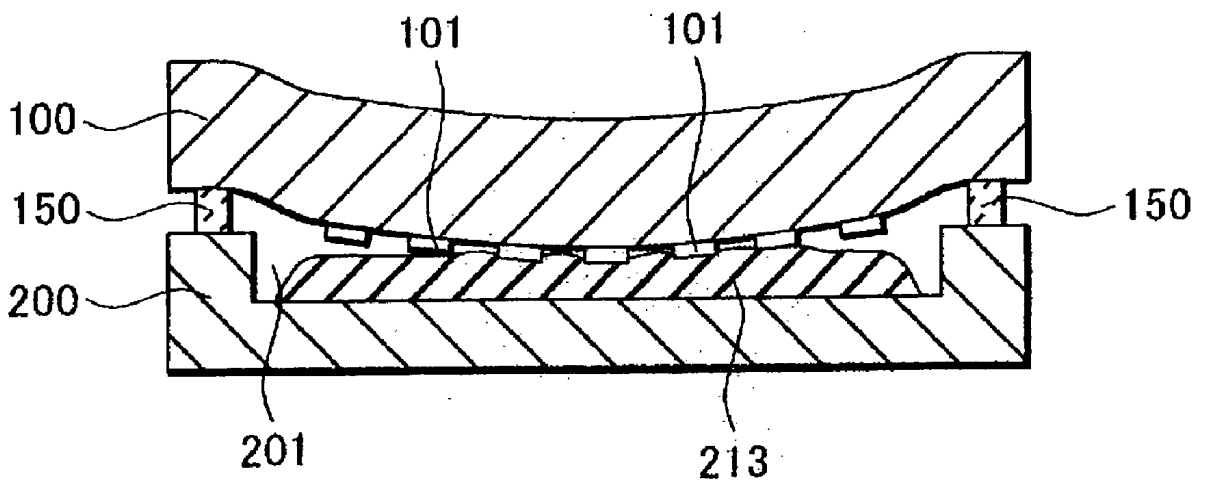
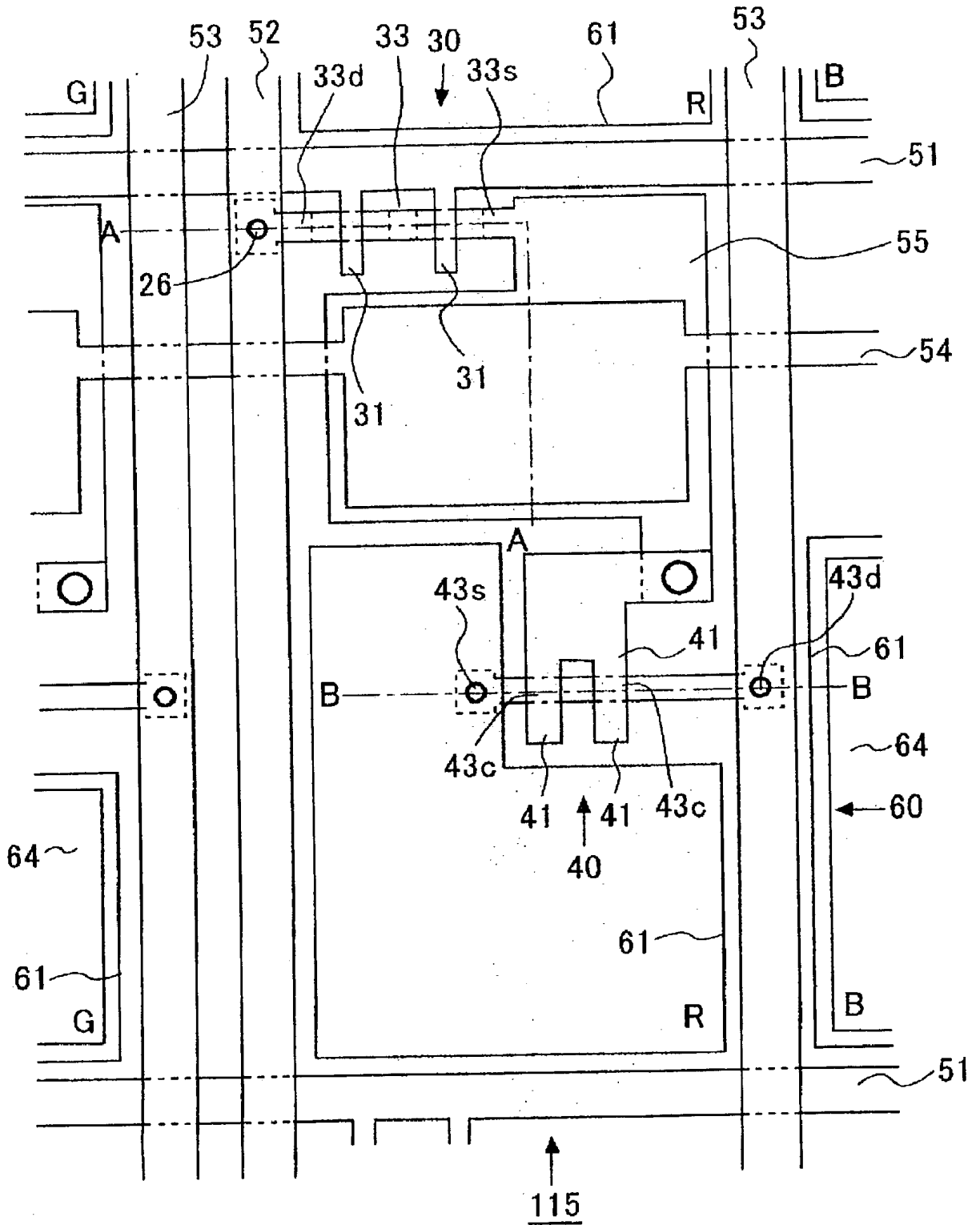
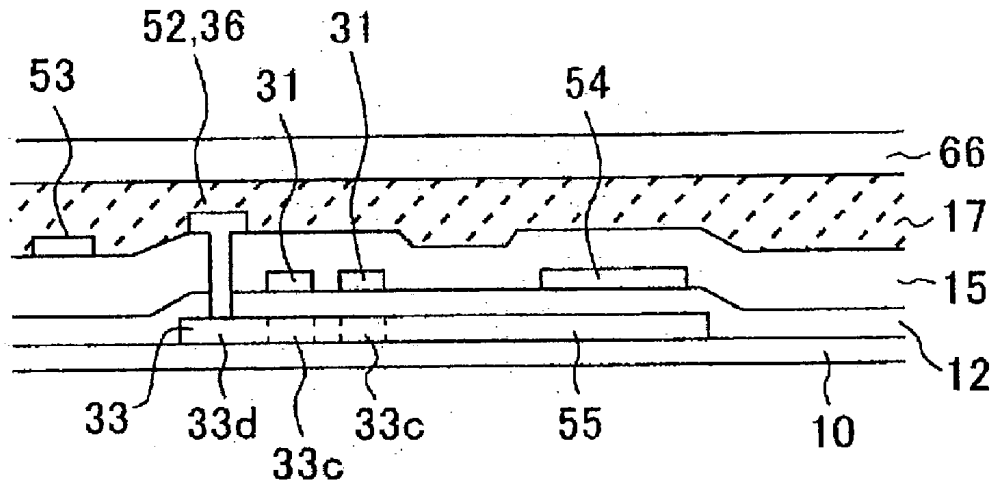


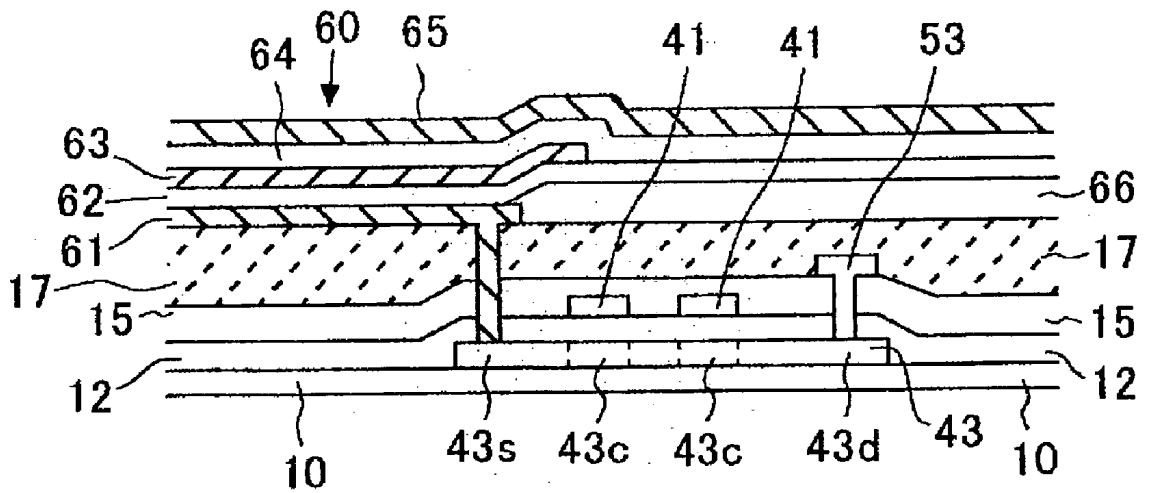
FIG. 7



**FIG. 8A**

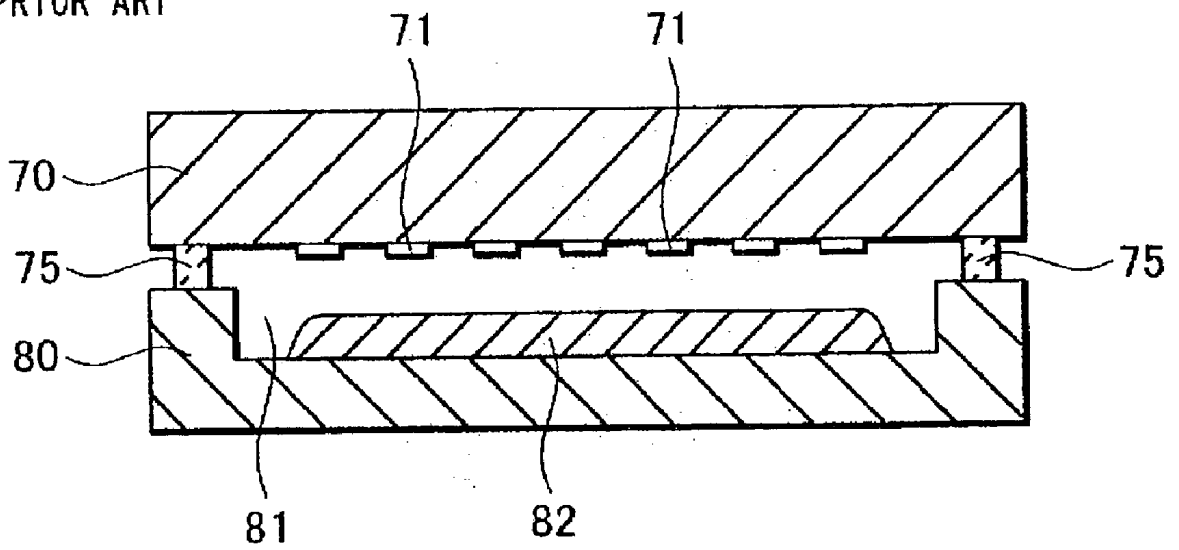


**FIG. 8B**



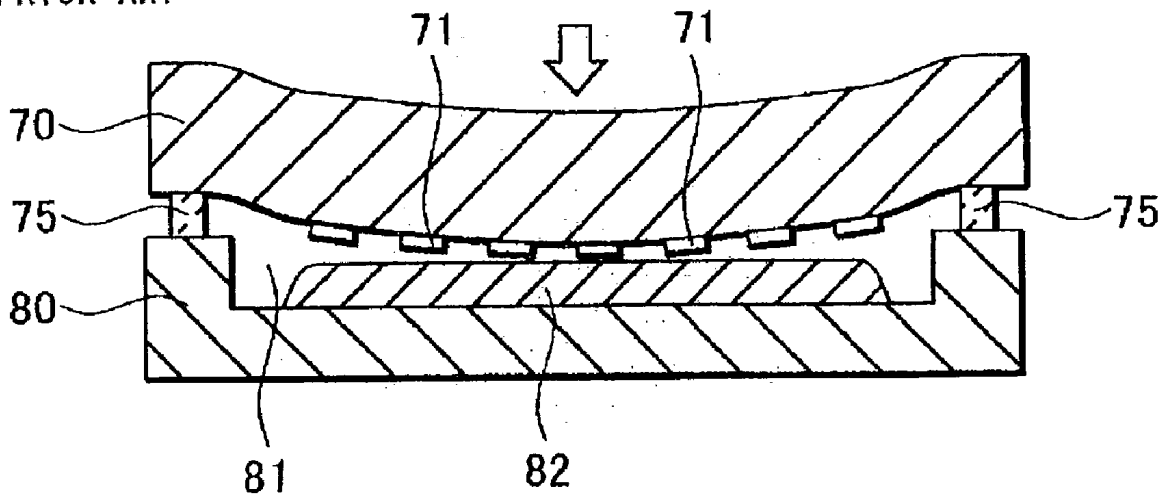
**FIG. 9**

PRIOR ART



**FIG. 10**

PRIOR ART



## ELECTROLUMINESCENT DISPLAY DEVICE

### BACKGROUND OF THE INVENTION

[0001] 1. Field of the Invention

[0002] This invention relates to an electroluminescent display device, particularly to a sealing structure of the electroluminescent display device.

[0003] 2. Description of the Related Art

[0004] In recent years, electroluminescent (hereafter, referred to as an EL) display devices with EL elements have been receiving an attention as a display device substituting a CRT and an LCD.

[0005] Since the EL element is sensitive to moisture, there has been known an EL display panel structure in which the EL element is covered with a metal cap or a glass cap coated with a desiccant. FIG. 9 is a cross-sectional view showing such a conventional structure of the EL display panel.

[0006] A first glass substrate 70 has a display region formed with many EL elements 71 thereon. The first glass substrate 70 is attached to a second glass substrate 80 working as a cap with sealing resin 75 made of an epoxy resin. The second glass substrate 80 has a concave portion 81 (hereafter, referred to as a pocket portion 81) in a region corresponding to the above display region. The pocket portion 81 is coated with a desiccant layer 82 for absorbing moisture.

[0007] Here, the forming of the pocket portion 81 is for securing a space between the desiccant layer 82 and the EL element 71, thereby preventing the EL element 71 from being contacted by the desiccant layer 82, which may result in damaging the EL element 71.

[0008] As shown in FIG. 10, however, an external force can be applied to a surface of the first glass substrate 70. This can occur even in a manufacturing process of the EL display device (for example, a process of conveying a glass substrate) and also when a panel surface of the EL display device is touched by a user. This external force causes flexure in the first glass substrate 70, and the desiccant layer 82 and the EL element 71 contact each other. With the application of the further external force, the EL element 71 may be broken by stress from the desiccant layer 82. Furthermore, the same problems are caused by applying of the external force to a surface of the second glass substrate 80.

### SUMMARY OF THE INVENTION

[0009] The invention provides an electroluminescent display device that includes a first substrate having an electroluminescent element thereon, a second substrate attached to the first substrate, a desiccant layer disposed on the second substrate so that the desiccant layer faces the first substrate, and a stress buffer layer covering the desiccant layer.

[0010] The invention also provides an electroluminescent display device that includes a first substrate having an electroluminescent element thereon, a second substrate attached to the first substrate, and a desiccant layer disposed on the second substrate so that the desiccant layer faces the first substrate. The desiccant layer has an elastic coefficient

low enough to absorb mechanical stresses generated by the electroluminescent element when it contacts the desiccant layer under an application of an external force to the display device.

### BRIEF DESCRIPTION OF THE DRAWINGS

[0011] FIG. 1 is a plan view of an electroluminescent display device according to a first embodiment of the invention.

[0012] FIG. 2 is a cross-sectional view of the device of FIG. 1 along line A-A of FIG. 1.

[0013] FIG. 3 is a perspective view of a stress buffer layer of the first embodiment of the invention.

[0014] FIG. 4 is a cross-sectional view of the electroluminescent display device of FIG. 1 under application of an external force.

[0015] FIG. 5 is a cross-sectional view of an electroluminescent display device according to a second embodiment of the invention.

[0016] FIG. 6 is a cross-sectional view of the electroluminescent display device of FIG. 5 under application of an external force.

[0017] FIG. 7 is a plan view of a pixel of the display devices of the first and second embodiments.

[0018] FIGS. 8A and 8B are cross-sectional views of the pixel of the organic EL display device of FIG. 7.

[0019] FIG. 9 is a cross-sectional view of a conventional electroluminescent display device.

[0020] FIG. 10 is a cross-sectional view of the electroluminescent display device of FIG. 9 a cross-sectional view of the electroluminescent display device of FIG. 1 under application of an external force.

### DETAILED DESCRIPTION OF THE INVENTION

[0021] FIG. 1 is a plan view of an electroluminescent display device according to a first embodiment of the invention. FIG. 2 is a cross-sectional view along line A-A of FIG. 1.

[0022] A first glass substrate 100 (a display panel) has a display region formed with many EL elements 101 on a surface thereof. The thickness of the first glass substrate 100 is approximately 0.7 mm. In this display region, a plurality of pixels is disposed in a matrix and the EL element 101 is disposed in each of those pixels.

[0023] A second glass substrate 200 is a glass substrate for sealing the above mentioned first glass substrate 100 and its thickness is approximately 0.7 mm. This second glass substrate 200 has a concave portion 201 (hereafter, referred to as a pocket portion 201) in a region corresponding to the display region, which is formed by etching. The depth of the pocket portion 201 is approximately 0.3 mm.

[0024] There is coated in the pocket portion 201 a desiccant layer 210 for absorbing moisture. The desiccant layer 210 is formed, for example, by coating a solvent dissolved with powdered calcium oxide or barium oxide and resin as

an adhesive on a bottom of the pocket portion 201 and then hardening the solvent by UV irradiation or heating.

[0025] The desiccant layer 210 is covered with a stress buffer layer 211. The stress buffer layer 211 is formed, for example, by coating the desiccant layer 210 with an epoxy resin or by covering the desiccant layer 210 with a sheet having elasticity made of, for example, polyethylene terephthalate (PET) or fluoroplastic.

[0026] Furthermore, the stress buffer layer 211 is preferably has many air vents 212 as shown in FIG. 3. This is for keeping air permeability of the desiccant layer 210 high to prevent it from losing the function as a desiccant.

[0027] The first glass substrate 100 and the second glass substrate 200 are attached with sealing resin 150 made of an epoxy resin in a chamber of N<sub>2</sub> gas atmosphere. Thus, N<sub>2</sub> gas fills a space surrounded by the stress buffer layer 211, the first glass substrate 100 and the sealing resin 150 to form an N<sub>2</sub> gas layer 102.

[0028] According to this embodiment, the electroluminescent display device has a structure in which the stress buffer layer 211 is disposed between the desiccant layer 210 and the EL element 101. Therefore, as shown in FIG. 4, when an external force is applied to the first glass substrate 100 to cause flexure therein, and the EL element 101 and the stress buffer layer 211 contact each other, elastic deformation occurs in the stress buffer layer 211 so that the stress applied to the EL element 101 is dispersed and absorbed by this stress buffer layer 211, thereby preventing the breaking of the EL element 101.

[0029] Second Embodiment

[0030] FIG. 5 is a cross-sectional view showing an electroluminescent display device according to a second embodiment of the invention. FIG. 5 corresponds to a cross-sectional view along line A-A' of FIG. 1. Note that the same numerals are given to the same portions as those of FIG. 2.

[0031] While in the first embodiment the desiccant layer 210 is covered with the stress buffer layer 211, in this embodiment the elasticity is provided in the desiccant layer 213 itself, thereby relaxing the stress applied to the EL element 101.

[0032] The desiccant layer 213 is formed by coating a solvent dissolved with powdered calcium oxide or barium oxide and a resin as an adhesive on a bottom of the pocket portion 201 and then hardening the solvent by UV irradiation or heating. Here, the amount of the resin in this desiccant layer 213 is increased to 20 or more weight % for increasing the elasticity. Epoxy resin or UV resin is appropriate as the resin.

[0033] Consequently, as shown in FIG. 6, when an external force is applied to the first glass substrate 100 to cause flexure therein, and the EL element 101 and the desiccant layer 213 contact each other, elastic deformation occurs in the desiccant layer 213 itself so that the stress applied to the EL element 101 is dispersed and absorbed by the desiccant layer 213, thereby preventing the breaking of the EL element 101.

[0034] Next, there is described an example of structures of the pixel of the EL display device applied to the first and second embodiments described above.

[0035] FIG. 7 is a plan view showing a pixel of an organic EL display device. FIG. 8A is a cross-sectional view along line A-A of FIG. 7 and FIG. 8B is a cross-sectional view along line B-B of FIG. 7.

[0036] As shown in FIG. 7, a pixel 115 is formed in a region enclosed with a gate signal line 51 and a drain signal line 52. A plurality of the pixels 115 is disposed in a matrix.

[0037] There are disposed in the pixel 115 an organic EL element 60 as a self-emission device, a switching TFT (thin film transistor) 30 for controlling a timing of supplying an electric current to the organic EL element 60, a driving TFT 40 for supplying an electric current to the organic EL element 60 and a storage capacitor. The organic EL element 60 includes an anode 61, an emissive made of an emission material and a cathode 65.

[0038] The switching TFT 30 is provided in a periphery of a point of intersection of the both signal lines 51 and 52. A source 33s of the switching TFT 30 serves as a capacitor electrode 55 for forming a capacitor with a storage capacitor electrode line 54 and is connected to a gate electrode 41 of the driving TFT 40. A source 43s of the driving TFT 40 is connected to the anode 61 of the organic EL element 60, while a drain 43d is connected to a driving source line 53 as a current source to be supplied to the organic EL element 60.

[0039] The storage capacitor electrode line 54 is disposed in parallel with the gate signal line 51. The storage capacitor electrode line 54 is made of Cr (chromium) etc and forms a capacitor by storing an electric charge with the capacitor electrode 55 connected to the source 33s of the TFT through a gate insulating film 12. The storage capacitor 56 is provided for storing voltage applied to the gate electrode 41 of the driving TFT 40.

[0040] As shown in FIGS. 8A and 8B, the organic EL display device is formed by laminating the TFTs and the organic EL element sequentially on a substrate 10 such as a substrate made of a glass or a synthetic resin, a conductive substrate, or a semiconductor substrate. When using a conductive substrate or a semiconductor substrate as the substrate 10, however, an insulating film such as SiO<sub>2</sub> or SiN<sub>x</sub> is formed on the substrate 10, and then the switching TFT 30, the driving TFT 40 and the organic EL element 60 are formed thereon. Each of the two TFTs has a so-called top gate structure in which a gate electrode is disposed above an active layer with a gate insulating film being interposed therebetween.

[0041] There will be described the switching TFT 30 first. As shown in FIG. 8A, an amorphous silicon film (hereafter, referred to as an a-Si film) is formed on the insulating substrate 10 made of a silica glass or a non-alkali glass by a CVD method. The a-Si film is irradiated by laser beams for melting and recrystallizing to form a poly-silicon film (hereafter, referred to as a p-Si film) as an active layer 33. On the active layer 33, a single-layer or a multi-layer of an SiO<sub>2</sub> film and an SiN<sub>x</sub> film is formed as the gate insulating film 12. There are disposed on the gate insulating film 12 the gate signal line 51 made of metal having a high melting point such as Cr or Mo (molybdenum) and also serving as a gate electrode 31, the drain signal line 52 made of Al (aluminum), and the driving source line 53 made of Al and serving as a driving source of the organic EL element.

[0042] An interlayer insulating film 15 laminated with an SiO<sub>2</sub> film, an SiN<sub>x</sub> film and an SiO<sub>2</sub> film sequentially is

formed on the whole surfaces of the gate insulating film **12** and the active layer **33**. There is provided a drain electrode **36** by filling metal such as Al in a contact hole provided correspondingly to a drain **33d**. Furthermore, a planarization insulation film **17** for planarizing a surface which is made of organic resin is formed on the whole surface.

[0043] Next, there will be described the driving TFT **40** of the organic EL element. As shown in FIG. 8B, an active layer **43** formed by poly-crystalizing an a-Si film by irradiating laser beams thereto, the gate insulating film **12**, and the gate electrode **41** made of metal having a high melting point such as Cr or Mo are formed sequentially on the insulating substrate **10**. There are provided in the active layer **43** a channel **43c**, and a source **43s** and a drain **43d** on both sides of the channel **43c**. The interlayer insulating film **15** is formed on the whole surfaces of the gate insulating film **12** and the active layer **43**. There is disposed the driving source line **53** connected to a driving source by filling metal such as Al in a contact hole provided correspondingly to a drain **43d**. Furthermore, a planarization insulation film **17** for planarizing the surface, which is made of, for example, an organic resin is formed on the whole surface. A contact hole is formed in a position corresponding to a source **43s** in the planarization insulation film **17**. There is formed on the planarization insulation film **17** a transparent electrode made of ITO (Indium Tin Oxide) and contacting to the source **43s** through the contact hole, i.e., the anode **61** of the organic EL element. The anode **61** is formed in each of the pixels, being isolated as an island.

[0044] The organic EL element **60** has a structure of laminating sequentially the anode **61** made of a transparent electrode such as ITO, a hole transport layer **62** including a first hole transport layer made of MTDATA (4, 4-bis (3-methylphenylphenylamino) biphenyl) and a second hole transport layer made of TPD (4, 4, 4-tris (3-methylphenylphenylamino) triphenylamine), an emissive **63** made of Bebq<sub>2</sub> (bis(10-hydroxybenzo[h]quinolinato)beryllium) containing a quinacridone derivative, an electron transport layer **64** made of Bebq<sub>2</sub>, and a cathode **65** made of magnesium-indium alloy, aluminum or aluminum alloy.

[0045] Incidentally, the planarization insulation film **17** is formed with a second planarization insulation film **66** thereon. The second planarization insulation film **66** is removed on the anode **61**.

[0046] In the organic EL element **60**, a hole injected from the anode **61** and an electron injected from the cathode **65** are recombined in the emissive and an exciton is formed by exciting an organic module forming the emissive **63**. Light is emitted from the emissive **63** in a process of radiation of the exciton and then released outside after going through the

transparent anode **61** to the transparent insulating substrate **10**, thereby to complete light-emission.

[0047] According to this embodiment, in the sealing structure of the electroluminescent display device in which the first glass substrate (a display panel) having the EL element and the second glass substrate for sealing the EL element are attached together, the stress buffer layer is disposed between the desiccant layer and the EL element, thereby preventing the breaking of the EL element **101** when external force is applied to the first glass substrate or the second glass substrate. Furthermore, the amount of the resin in the desiccant layer is increased so that the same effect is obtained without using the stress buffer layer.

What is claimed is:

1. An electroluminescent display device comprising:
  - a first substrate having an electroluminescent element thereon;
  - a second substrate attached to the first substrate;
  - a desiccant layer disposed on the second substrate so that the desiccant layer faces the first substrate; and
  - a stress buffer layer covering the desiccant layer.
2. The electroluminescent display device of claim 1, wherein the stress buffer layer is made of a resin.
3. The electroluminescent display device of claim 1, wherein the stress buffer layer includes a plurality of air vents.
4. The electroluminescent display device of claim 2, wherein the stress buffer layer includes a plurality of air vents.
5. The electroluminescent display device of claim 1, wherein the second substrate includes a concave portion and the desiccant layer is disposed in the concave portion.
6. An electroluminescent display device comprising:
  - a first substrate having an electroluminescent element thereon;
  - a second substrate attached to the first substrate; and
  - a desiccant layer disposed on the second substrate so that the desiccant layer faces the first substrate, the desiccant layer having an elastic coefficient low enough to absorb mechanical stresses generated by the electroluminescent element contacting the desiccant layer under an application of an external force to the display device.
7. The electroluminescent display device of claim 6, wherein the desiccant layer includes a resin and the content of the resin in the desiccant layer is 20% by weight or higher.
8. The electroluminescent display device of claim 7, wherein the resin is an epoxy resin or an UV resin.

\* \* \* \* \*

专利名称(译)	电致发光显示装置		
公开(公告)号	<a href="#">US20040012332A1</a>	公开(公告)日	2004-01-22
申请号	US10/419982	申请日	2003-04-22
[标]申请(专利权)人(译)	三洋电机株式会社		
申请(专利权)人(译)	SANYO ELECTRIC CO., LTD.		
当前申请(专利权)人(译)	SANYO ELECTRIC CO., LTD.		
[标]发明人	SASATANI TORU OMURA TETSUJI		
发明人	SASATANI, TORU OMURA, TETSUJI		
IPC分类号	H05B33/04 H01L27/32 H01L51/50 H01L51/52 H05B33/00		
CPC分类号	H01L51/5237 H01L27/3244 H01L51/5259		
优先权	2002122114 2002-04-24 JP		
其他公开文献	US6930449		
外部链接	<a href="#">Espacenet</a> <a href="#">USPTO</a>		

摘要(译)

在电致发光显示装置的密封结构中，其中形成有EL元件的第一玻璃基板和作为盖的第二玻璃基板彼此连接，当外力施加到第一玻璃基板上时，防止了元件装置的断裂。玻璃基板和第二玻璃基板。密封结构具有在其表面上设置有EL元件的第一玻璃基板，利用密封树脂附接到第一玻璃基板的第二玻璃基板，形成在第二玻璃基板的表面上的干燥剂层和应力缓冲层覆盖干燥剂层的表面。

